

ORDERING INFORMATION

Device	Temperature Range	Package
MC1550F	-55°C to +125°C	Ceramic Flat
MC1550G	-55°C to +125°C	Metal Can

RF - IF AMPLIFIER

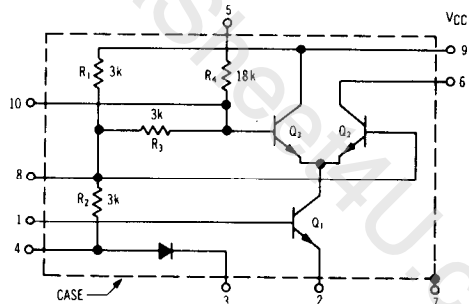
... a versatile, common-emitter, common-base cascode circuit for use in communications applications. See Application Note AN-215A for additional information.

- Constant Input Impedance over entire AGC range
- Extremely Low $\gamma_{12} = 4.3 \mu\text{mhos}$ at 60 MHz
- High Power Gain - 30 dB @ 60 MHz (0.5 MHz BW)
- Good Noise Figure - 5 dB @ 60 MHz

MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Power Supply Voltage, Pin 9	V_{CC}	20	Vdc
AGC Supply Voltage	V_{AGC}	20	Vdc
Input Differential Voltage, Pin 1 to Pin 4 ($R_S = 500 \text{ ohms}$)	V_{ID}	± 5.0	V(rms)
Power Dissipation (Package Limitation)	P_D		
Metal Can		680	mW
Derate above $T_A = +25^\circ\text{C}$		4.6	mW/ $^\circ\text{C}$
Flat Package		500	mW
Derate above $T_A = +25^\circ\text{C}$		3.3	mW/ $^\circ\text{C}$
Operating Ambient Temperature Range	T_A	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

CIRCUIT SCHEMATIC

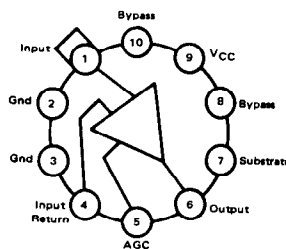


MC1550G

RF - IF AMPLIFIER SILICON MONOLITHIC INTEGRATED CIRCUIT



G SUFFIX
METAL PACKAGE
CASE 603B



ELECTRICAL CHARACTERISTICS

Characteristic

DC CHARACTERISTICS

Output Voltage

Test Voltage

Supply Drain Current

AGC Supply Drain Current

SMALL-SIGNAL CHARACTERISTICS

Small-Signal Voltage Gain

Bandwidth

Transducer Power Gain

FIGURE 1 - DC CHARACTERISTICS

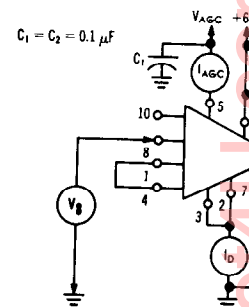
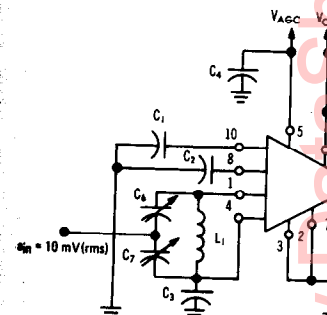


FIGURE 3 - POWER GAIN TEST

CIRCUIT DESCRIPTION

The MC1550 is built with monolithic fabrication techniques utilizing diffused resistors and small-geometry transistors. Excellent AGC performance is obtained by shunting the signal through the AGC transistor Q_3 , maintaining the operating point of the input transistor Q_1 . This keeps the input impedance constant over the entire AGC range.

The amplifier is intended to be used in a common-emitter, common-base configuration (Q_1 and Q_2) with Q_3 acting as an AGC transistor. The input signal is applied between pins 1 and 4, where pin 4 is ac-coupled to ground. DC source resistance between pins 1 and 4 should be small (less than 100 ohms). Pins 2 and 3 should be connected together and grounded. Pins 8 and 10 should be bypassed to ground. The positive supply voltage is applied at pin 9 and at higher frequencies, pin 9 should also be bypassed to ground. The output is taken between pins 6 and 9. The substrate is connected to pin 7 and should be grounded. AGC voltage is applied to pin 5.

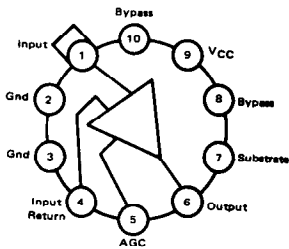


MC1550G

RF - IF AMPLIFIER SILICON MONOLITHIC INTEGRATED CIRCUIT



G SUFFIX
METAL PACKAGE
CASE 603B



CIRCUIT DESCRIPTION

The MC1550 is built with monolithic fabrication techniques using fused resistors and small-geometry transistors. Good GC performance is obtained by shunting the signal to the AGC transistor Q_1 , maintaining the operating point of the input transistor Q_2 . This keeps the input impedance constant over the entire AGC range.

The amplifier is intended to be used in a common-emitter, push-pull configuration (Q_1 and Q_2) with Q_1 acting as an emitter follower. The input signal is applied between pins 1 and 4. Pin 4 is ac-coupled to ground. DC source resistance at pins 1 and 4 should be small (less than 100 ohms). Pins 3 and 7 should be connected together and grounded. Pins 8 and 9 should be bypassed to ground. The positive supply applied at pin 9 and at higher frequencies, pin 9 should be bypassed to ground. The output is taken between pins 6 and 9. The substrate is connected to pin 7 and grounded. AGC voltage is applied to pin 5.

MC1550G

ELECTRICAL CHARACTERISTICS ($V^+ = +6$ Vdc, $T_A = +25^\circ\text{C}$)

Characteristic	Conditions	Figure	Symbol	Min	Typ	Max	Unit
DC CHARACTERISTICS							
Output Voltage	$V_{AGC} = 0$ Vdc $V_{AGC} = +6$ Vdc	1	V_O	3.80 5.90	—	4.65 6.00	Vdc
Test Voltage	$V_{AGC} = 0$ Vdc $V_{AGC} = +6$ Vdc	1	V_B	2.85 3.25	—	3.40 3.80	Vdc
Supply Drain Current	$V_{AGC} = 0$ Vdc $V_{AGC} = +6$ Vdc	1	I_D	— —	—	2.2 2.5	mAdc
AGC Supply Drain Current	$V_{AGC} = 0$ Vdc $V_{AGC} = +6$ Vdc	1	I_{AGC}	— —	—	-0.2 0.18	mAdc
SMALL-SIGNAL CHARACTERISTICS							
Small-Signal Voltage Gain	$f = 500$ kHz	2	A_V	22	—	29	dB
Bandwidth	-3.0 dB	2	BW	22	—	—	MHz
Transducer Power Gain	$f = 60$ MHz, BW = 6 MHz $f = 100$ MHz, BW = 6 MHz	3	A_P	—	25 21	—	dB

TYPICAL CHARACTERISTICS

($V_{CC} = 6.0$ Vdc, $T_A = +25^\circ\text{C}$ unless otherwise noted.)

FIGURE 1 - DC CHARACTERISTICS TEST CIRCUIT

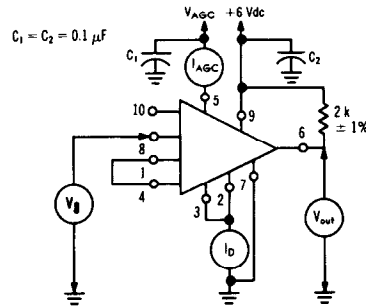


FIGURE 3 - POWER GAIN TEST CIRCUIT @ 60 MHz

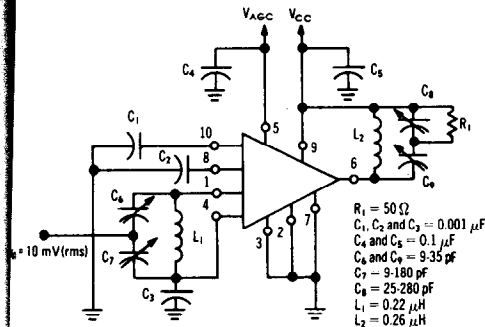


FIGURE 2 - VOLTAGE GAIN AND BANDWIDTH TEST CIRCUIT

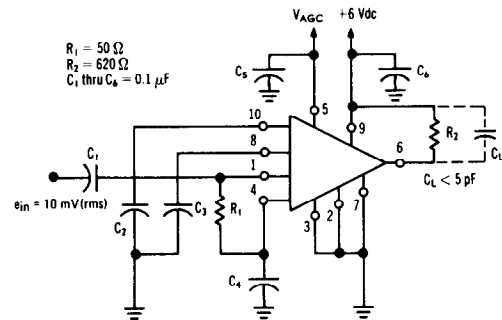
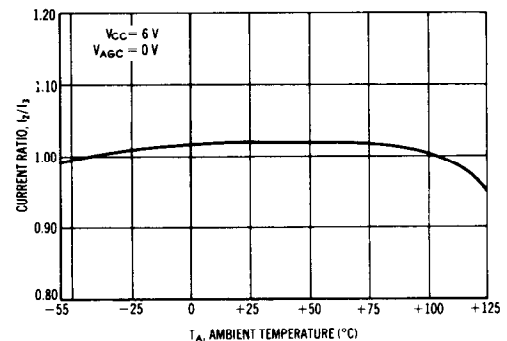


FIGURE 4 - DRAIN CURRENT TEMPERATURE CHARACTERISTICS



TYPICAL CHARACTERISTICS (continued)

FIGURE 5 - INPUT RESISTANCE AND CAPACITANCE versus FREQUENCY

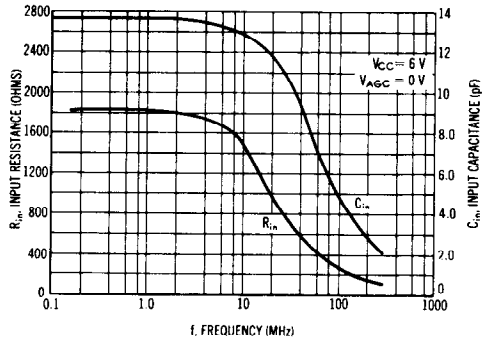


FIGURE 6 - INPUT RESISTANCE AND CAPACITANCE versus AGC VOLTAGE

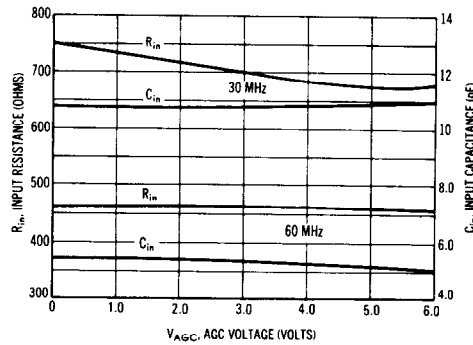


FIGURE 7 - OUTPUT RESISTANCE AND CAPACITANCE versus FREQUENCY

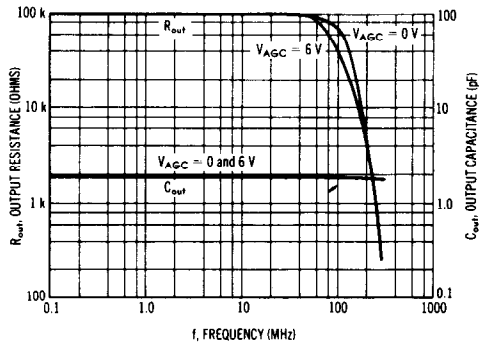


FIGURE 8 - OUTPUT RESISTANCE AND CAPACITANCE versus AGC VOLTAGE

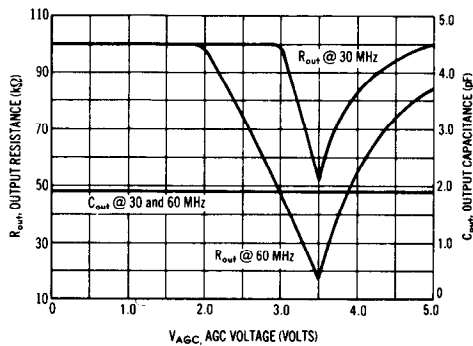


FIGURE 9 - MAXIMUM TRANSDUCER POWER GAIN versus FREQUENCY

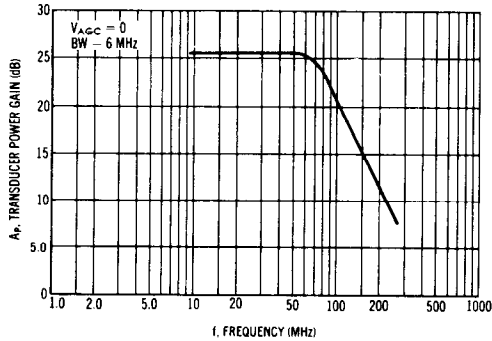


FIGURE 10 - TRANSDUCER POWER GAIN versus TEMPERATURE

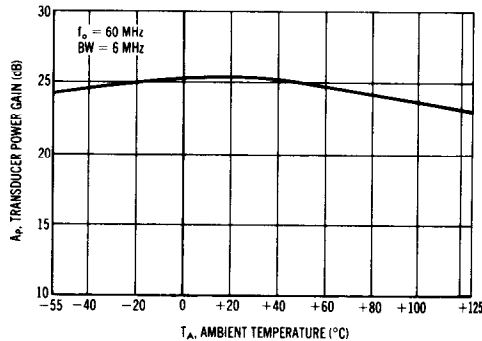


FIGURE 11

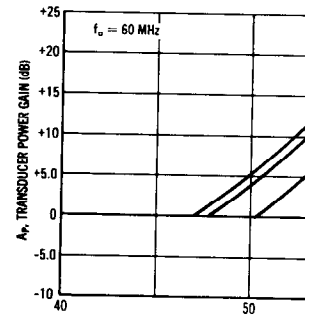


FIGURE 12 - NOISE FIGURE A RESISTANCE versus F

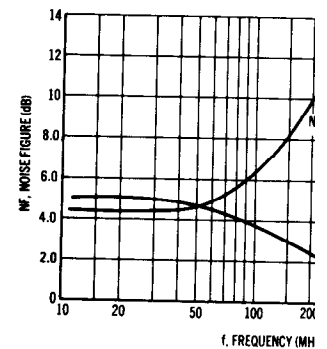
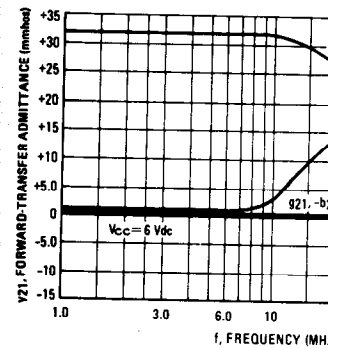
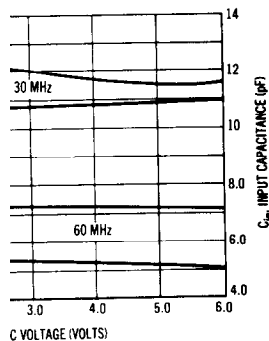


FIGURE 14 - y21, FORWARD-TRAN versus FREQUENCY

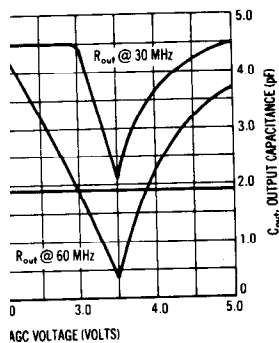


TYPICAL CHARACTERISTICS (continued)

INPUT RESISTANCE AND C_{in} versus AGC VOLTAGE



OUTPUT RESISTANCE AND C_{out} versus AGC VOLTAGE



TRANSDUCER POWER GAIN A_p versus TEMPERATURE

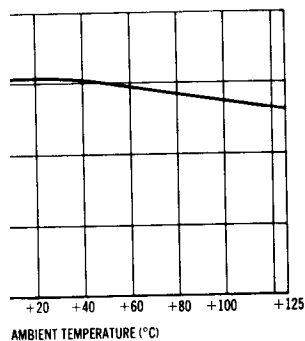


FIGURE 11 - TRANSDUCER POWER BANDWIDTH versus AGC VOLTAGE

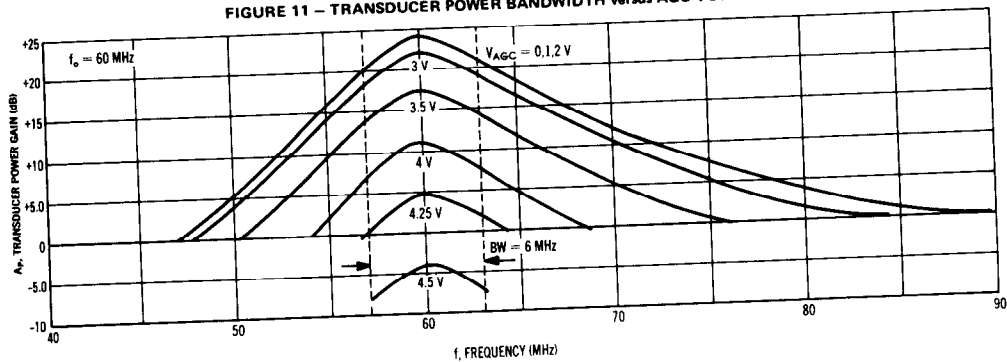


FIGURE 12 - NOISE FIGURE AND OPTIMUM SOURCE RESISTANCE versus FREQUENCY

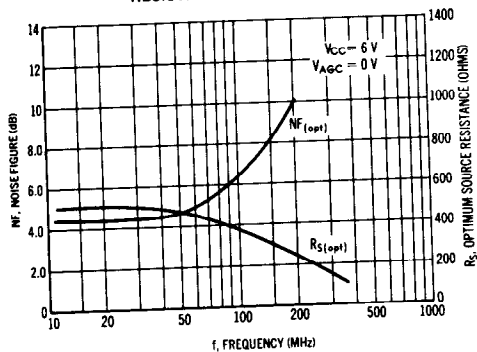


FIGURE 13 - NOISE FIGURE versus SOURCE RESISTANCE

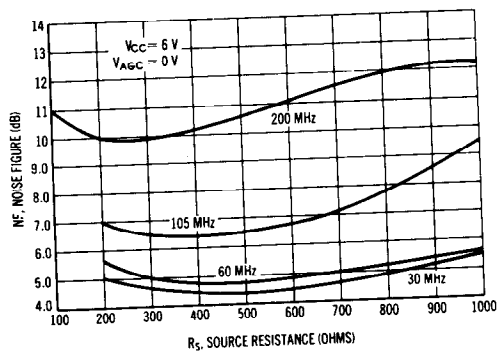


FIGURE 14 - Y_{21} , FORWARD-TRANSFER ADMITTANCE versus FREQUENCY

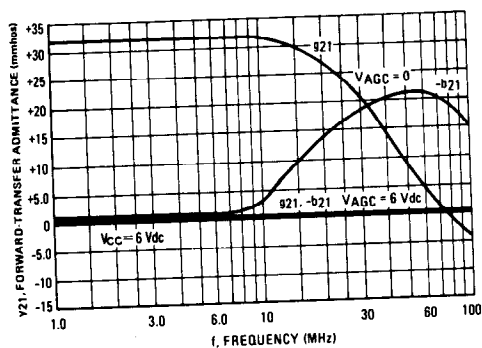
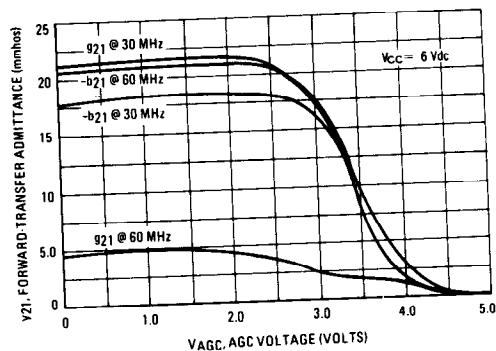
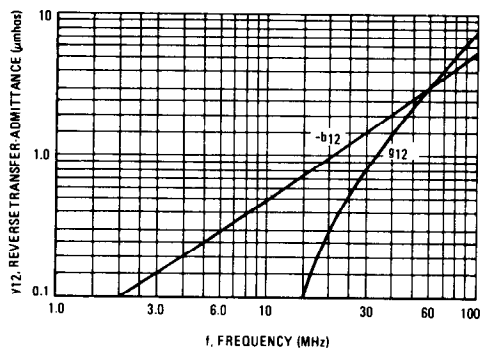
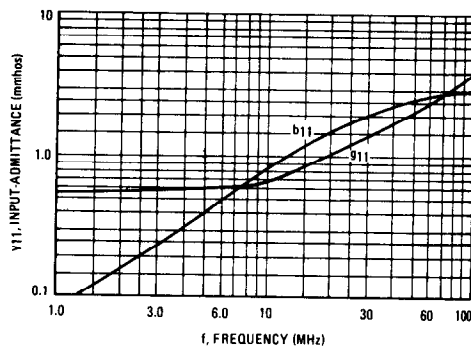
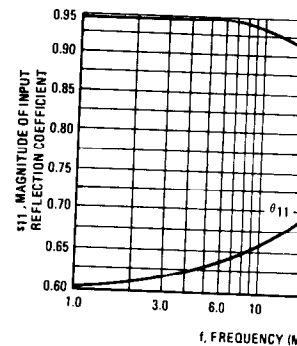
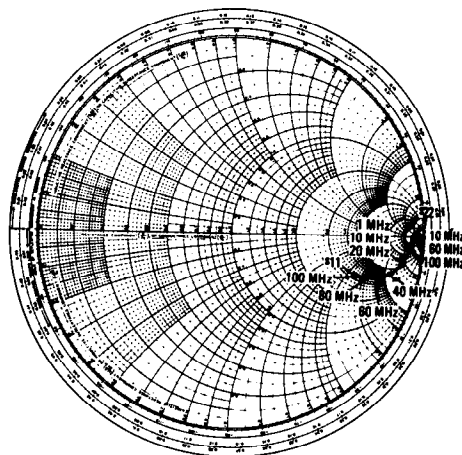
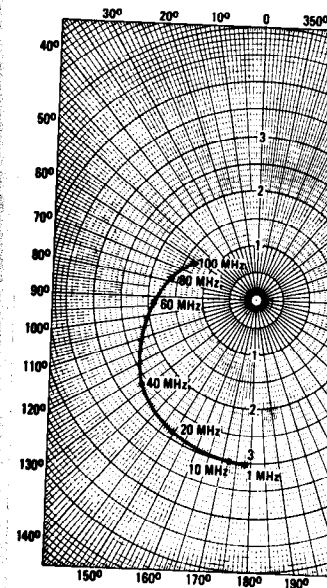


FIGURE 15 - Y_{21} , FORWARD-TRANSFER ADMITTANCE versus AGC VOLTAGE



TYPICAL CHARACTERISTICS

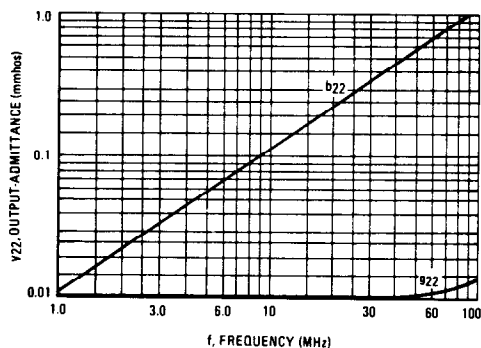
 $(V_{CC} = 6.0\text{Vdc}, T_A = +25^\circ\text{C}$ unless otherwise noted.)FIGURE 16 - y_{12} , REVERSE TRANSFER-ADMITTANCE versus FREQUENCYFIGURE 17 - y_{11} , INPUT-ADMITTANCE versus FREQUENCYFIGURE 20 - s_{11} , INPL COEFFICIENT versusFIGURE 19 - s_{11} AND s_{22} , INPUT AND OUTPUT REFLECTION COEFFICIENTFIGURE 22 - s_{21} , FORWARD COEFFICIENT (

The y_{12} shown in Figure 16 illustrates the extremely low feedback of the MC1550 with no contribution from the external mounting circuitry. However, in many cases the external circuitry may contribute as much or more to the total feedback than does the MC1550.

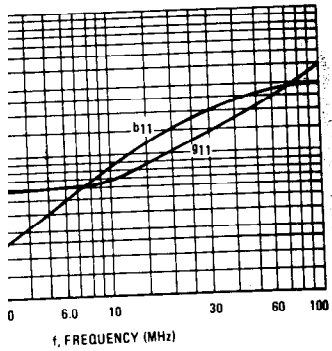
To perform more accurate design calculations of gain, stability, and input - output impedances it is recommended that the designer first determine the total feedback of device plus circuitry.

This can be done in one of two ways:

- (1) Measure the total y_{12} or s_{12} of the MC1550 installed in its mounting circuitry, or
- (2) Measure the y_{12} of the circuitry alone (without the MC1550 installed) and add the circuit y_{12} to the y_{12} for the MC1550 given in Figure 16.

FIGURE 18 - y_{22} , OUTPUT-ADMITTANCE versus FREQUENCY

INPUT ADMITTANCE versus FREQUENCY



9 - s_{11} AND s_{22} , INPUT AND OUTPUT REFLECTION COEFFICIENT

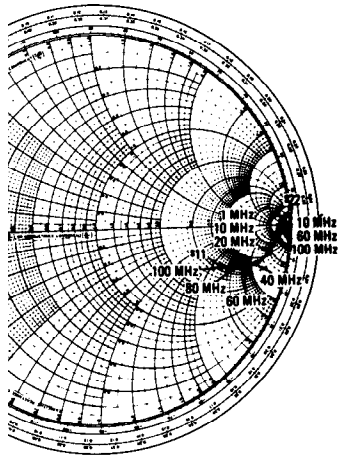


FIGURE 20 - s_{11} , INPUT REFLECTION COEFFICIENT versus FREQUENCY

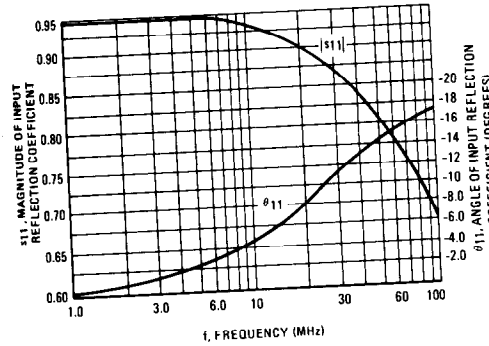


FIGURE 22 - s_{21} , FORWARD TRANSMISSION COEFFICIENT (GAIN)

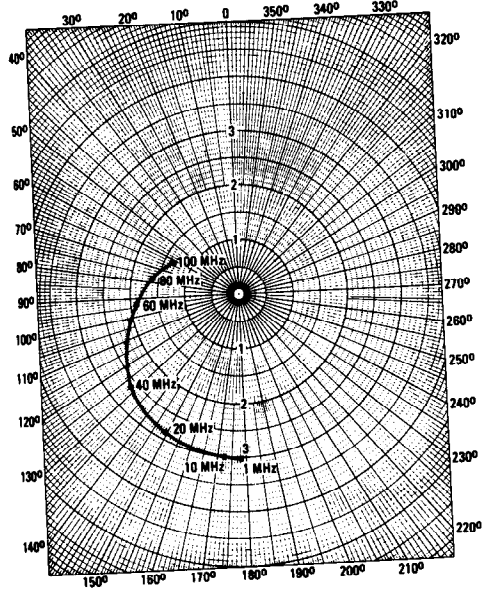


FIGURE 21 - s_{22} , OUTPUT REFLECTION COEFFICIENT versus FREQUENCY

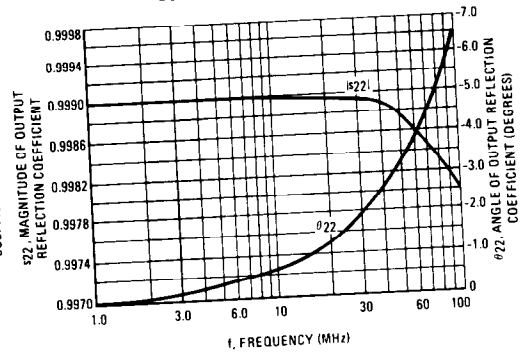


FIGURE 23 - s_{12} , REVERSE TRANSMISSION COEFFICIENT (FEEDBACK)

